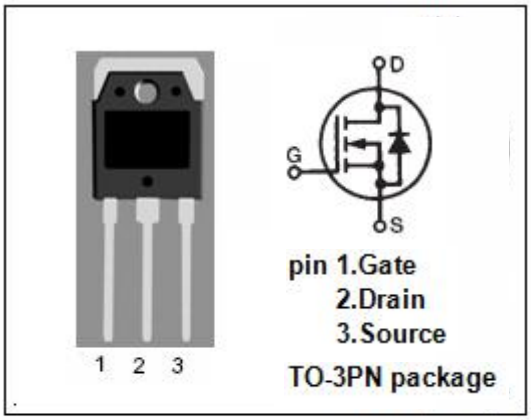
isc N-Channel MOSFET Transistor TK20J60W



• FEATURES

- Low drain-source on-resistance:
  $R_{DS}(ON) \leq 155m\Omega$
- Easy to control Gate switching
- Enhancement mode:
  Vth = 2.7 to 3.7V (V_{DS} = 10 V, I_D=1mA)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• DESCRIPTION

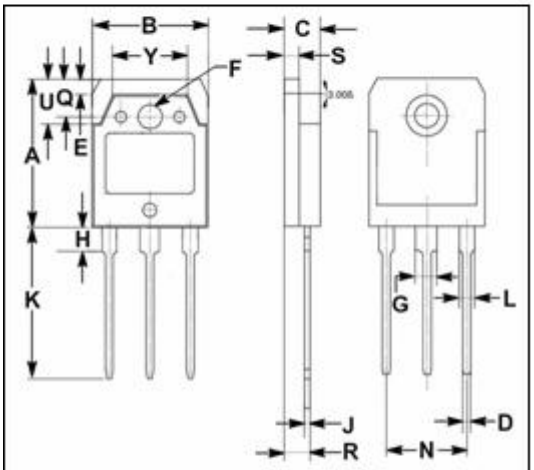
- Switching Voltage Regulators

• ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	600	V
V_{GS}	Gate-Source Voltage	±30	V
I_D	Drain Current-Continuous	20	A
I_{DM}	Drain Current-Single Pulsed	80	A
P_D	Total Dissipation @T_C=25℃	165	W
T_j	Max. Operating Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	0.757	℃/W



DIM	mm MIN	MAX
A	19.60	20.30
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	19.80	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

isc N-Channel MOSFET Transistor TK20J60W

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V; I_D= 10mA	600			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= 10V; I_D=1mA	2.7		3.7	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= 10V; I_D=10A			155	mΩ
I_{GSS}	Gate-Source Leakage Current	V_{GS}= ±30V;V_{DS}= 0V			±1	μA
I_{DSS}	Drain-Source Leakage Current	V_{DS}= 600V; V_{GS}= 0V			100	μA
V_{SDF}	Diode forward voltage	I_{DR} =20 A, V_{GS} = 0 V			1.7	V